International
IOR Rectifier

IRAM136-1060BS

iMOTION™ Series

10A, 600V

with Internal Shunt Resistor

Integrated Power Hybrid IC for
Appliance Motor Drive Applications

Description

International Rectifier's IRAM136-1060BS is a 10A, 600V Integrated Power Hybrid IC designed for advanced Appliance Motor Drives applications. Typical applications include energy efficient Washing Machine, Fans, Air Conditions and Refrigerator Compressor Drivers. This module offers an extremely compact, high performance AC motor-driver in an isolated package that simplifies design. Several built-in protection features such as over current, temperature monitoring, shoot through prevention and under voltage lockout makes this a very robust solution. The combination of highly efficient Trench IGBT technology and the industry benchmark 3-phase HVIC driver (3.3V/5V input compatible) and a fully isolated thermally enhanced package makes this a highly competitive solution. The compact Single in line (SIP05) package minimizes PCB space.

Features

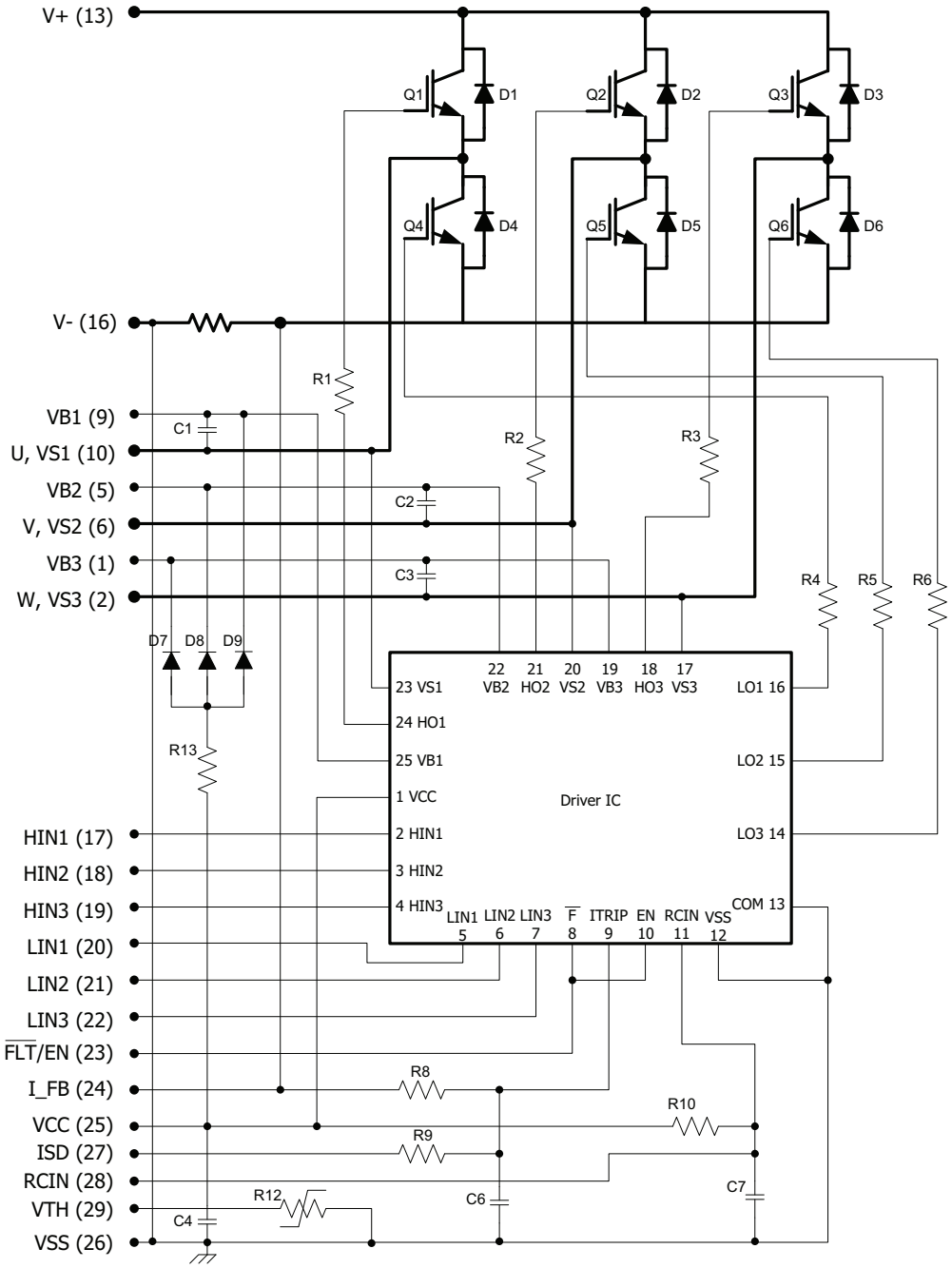
- Internal Shunt Resistor and current feedback
- Integrated gate drivers and bootstrap diodes
- Temperature feedback
- Programmable over current protection pin
- High efficiency Trench IGBT technology
- Under-voltage lockout for all channels
- Matched propagation delay for all channels
- 3.3V/5V Schmitt-triggered input logic
- Cross-conduction prevention logic
- Motor Power range 0.25~0.75kW / 85~253 Vac
- Isolation 2000V_{RMS} min and CTI> 600

Absolute Maximum Ratings

V_{CES} / V_{RRM}	IGBT/ FW Diode Blocking Voltage	600	V
V^+	Positive Bus Input Voltage	450	
I_o @ T_C=25°C	RMS Phase Current (Note 1)	10	A
I_o @ T_C=100°C	RMS Phase Current (Note 1)	5	
I_{pk}	Maximum Peak Phase Current (Note 2)	13	
F_p	Maximum PWM Carrier Frequency	20	kHz
P_d	Maximum Power dissipation per IGBT @ T_C =25°C	25	W
V_{ISO}	Isolation Voltage (1min)	2000	V_{RMS}
T_J (IGBT & Diode & IC)	Maximum Operating Junction Temperature	+150	°C
T_C	Operating Case Temperature Range	-20 to +100	
T_{STG}	Storage Temperature Range	-40 to +125	
T	Mounting torque Range (M3 screw)	0.8 to 1.0	Nm

Note 1: Sinusoidal Modulation at V^+=400V, T_J=150°C, F_{PWM}=16kHz, Modulation Depth=0.8, PF=0.6, See Figure 3.
Note 2: t_P<100ms, TC=25°C, F_{PWM}=16kHz.

Internal Electrical Schematic – IRAM136-1060BS



Absolute Maximum Ratings (Continued)

Symbol	Parameter	Min	Max	Units	Conditions
$P_{BR\ Peak}$	Bootstrap Resistor Peak Power (Single Pulse)	---	15.0	W	t_P=100µs, T_C =100°C ESR / ERJ series
$V_{S1,2,3}$	High side floating supply offset voltage	$V_{B1,2,3}$ - 25	$V_{B1,2,3}$ +0.3	V	
$V_{B1,2,3}$	High side floating supply voltage	-0.3	600	V	
V_{CC}	Low Side and logic fixed supply voltage	-0.3	20	V	
V_{IN}	Input voltage LIN, HIN, I_{Trip}	-0.3	Lower of (V_{SS}+15V) or V_{CC}+0.3V	V	

Inverter Section Electrical Characteristics @T_J= 25°C

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	---	---	V	V_{IN}=0V, I_C=250µA
$\Delta V_{(BR)CES}$ / ΔT	Temperature Coeff. Of Breakdown Voltage	---	0.3	---	V/°C	V_{IN}=0V, I_C=250µA (25°C - 150°C)
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	---	1.5	1.7	V	I_C=5A, T_J=25°C
		---	1.7	---		I_C=5A, T_J=150°C
I_{CES}	Zero Gate Voltage Collector Current	---	5	80	µA	V_{IN}=0V, V^+=600V
		---	80	---		V_{IN}=0V, V^+=600V, T_J=150°C
V_{FM}	Diode Forward Voltage Drop	--	1.8	2.35	V	I_F=5A
		---	1.45	---		I_F=5A, T_J=150°C
V_{BDFM}	Bootstrap Diode Forward Voltage Drop	--	1.2	---	V	I_F=1A
R_{BR}	Bootstrap Resistor Value	---	22	---	Ω	T_J=25°C
$\Delta R_{BR}/R_{BR}$	Bootstrap Resistor Tolerance	---	---	±5	%	T_J=25°C
I_{BUS_TRIP}	Current Protection Threshold (positive going)	---	9	---	A	ISD=Vss. See fig. 2 and fig. 11b
		---	7	---		ISD=Open. See fig. 2 and fig. 11b

Inverter Section Switching Characteristics @ T_J= 25°C

Symbol	Parameter	Min	Typ	Max	Units	Conditions
E_{ON}	Turn-On Switching Loss	---	240	400	µJ	I_C=5A, V^+=400V V_{CC}=15V, L=1.2mH Energy losses include "tail" and diode reverse recovery See CT1
E_{OFF}	Turn-Off Switching Loss	---	65	90		
E_{TOT}	Total Switching Loss	---	305	490		
E_{REC}	Diode Reverse Recovery energy	---	15	25		
t_{RR}	Diode Reverse Recovery time	---	115	---	ns	
E_{ON}	Turn-on Switching Loss	---	330	---	µJ	I_C=5A, V^+=400V V_{CC}=15V, L=1.2mH, T_J=150°C Energy losses include "tail" and diode reverse recovery See CT1
E_{OFF}	Turn-off Switching Loss	---	105	---		
E_{TOT}	Total Switching Loss	---	435	---		
E_{REC}	Diode Reverse Recovery energy	---	40	---		
t_{RR}	Diode Reverse Recovery time	---	150	---	ns	
Q_G	Turn-On IGBT Gate Charge	---	19	29	nC	I_C=8A, V^+=400V, V_{GE}=15V
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J=150°C, I_C=5A, V_P=600V V^+= 450V, V_{CC}=+15V to 0V See CT3
SCSOA	Short Circuit Safe Operating Area	5	---	---	µs	T_J=25°C, V_P=600V, V^+= 360V, V_{CC}=+15V to 0V See CT2
I_{CSC}	Short Circuit Collector Current	---	50	---	A	T_J=25°C, V^+= 400V, V_{CC}=15V See CT2

Recommended Operating Conditions Driver Function

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. All voltages are absolute referenced to COM. The V_S offset is tested with all supplies biased at 15V differential (Note 3)

Symbol	Definition	Min	Typ	Max	Units
$V_{B1,2,3}$	High side floating supply voltage	V_S+12	V_S+15	V_S+20	V
$V_{S1,2,3}$	High side floating supply offset voltage	Note 4	---	450	
V_{CC}	Low side and logic fixed supply voltage	12	15	20	V
V_{ITRIP}	I_{TRIP} input voltage	V_{SS}	---	V_{SS}+5	
V_{IN}	Logic input voltage LIN, HIN	V_{SS}	---	V_{SS}+5	V
HIN	High side PWM pulse width	1	---	---	µs
Deadtime	External dead time between HIN and LIN	1	---	---	µs

Note 3: For more details, see IR21364 data sheet

Note 4: Logic operational for V_s from COM-5V to COM+600V. Logic state held for V_s from COM-5V to COM-V_{BS}. (please refer to DT97-3 for more details)

Static Electrical Characteristics Driver Function @ T_J= 25°C

V_{BIAS} (V_{CC}, $V_{BS1,2,3}$)=15V, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to COM and are applicable to all six channels. (Note 3)

Symbol	Definition	Min	Typ	Max	Units
$V_{IN,th+}$	Positive going input threshold	2.5	---	---	V
$V_{IN,th-}$	Negative going input threshold	---	---	0.8	V
V_{CCUV+}, V_{BSUV+}	V_{CC} and V_{BS} supply undervoltage, Positive going threshold	10.6	11.1	11.6	V
V_{CCUV-}, V_{BSUV-}	V_{CC} and V_{BS} supply undervoltage, Negative going threshold	10.4	10.9	11.4	V
V_{CCUVH}, V_{BSUVH}	V_{CC} and V_{BS} supply undervoltage lock-out hysteresis	---	0.2	---	V
I_{QBS}	Quiescent V_{BS} supply current	---	---	120	µA
I_{QCC}	Quiescent V_{CC} supply current	---	---	4	mA
I_{LK}	Offset Supply Leakage Current	---	---	50	µA
I_{IN+}	Input bias current V_{IN}=3.3V	---	100	195	µA
I_{IN-}	Input bias current V_{IN}=0V	-1	--	---	µA
I_{TRIP+}	I_{TRIP} bias current $V_{T/ITRIP}$=3.3V	---	3.3	6	µA
I_{TRIP-}	I_{TRIP} bias current $V_{T/ITRIP}$=0V	-1	---	---	µA
$V(I_{TRIP})$	I_{TRIP} threshold Voltage	0.44	0.49	0.54	V
$V(I_{Trip}$, HYS)	I_{TRIP} Input Hysteresis	---	0.07	---	V

Dynamic Electrical Characteristics @ T_J= 25°C

Driver only timing unless otherwise specified.

Symbol	Parameter	Min	Typ	Max	Units	Conditions
T_{ON}	Input to Output propagation turn-on delay time (see fig.11)	---	---	1.15	µs	I_C=5A, V^+=300V
T_{OFF}	Input to Output propagation turn-off delay time (see fig. 11)	---	---	1.15	µs	
T_{FLT}	Input Filter Time (HIN, LIN)	100	200	---	ns	V_{IN}=0 or V_{IN}=5V
$T_{BLT-ITRIP}$	I_{TRIP} Blanking Time	100	150	---	ns	V_{IN}=0 or V_{IN}=5V, V_{ITRIP}=5V
D_T	Dead Time	220	290	360	ns	V_{IN}=0 or V_{IN}=5V
M_T	Matching Propagation Delay Time (On & Off) all channels	---	40	75	ns	External dead time> 400ns
T_{ITRIP}	I_{TRIP} to six switch turn-off propagation delay (see fig. 2)	---	---	1.75	µs	I_C=5A, V^+=300V
$T_{FLT-CLR}$	FAULT clear time (see fig. 2)	---	32.0	---	ms	T_C = 25°C

Thermal and Mechanical Characteristics

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$R_{th(J-C)}$	Thermal resistance, per IGBT	---	4.6	5.0	°C/W	Inverter Operating Condition Flat, greased surface. Heatsink compound thermal conductivity 1W/mK
$R_{th(J-C)}$	Thermal resistance, per Diode	---	6.9	7.6		
$R_{th(C-S)}$	Thermal resistance, C-S	---	0.1	---		
C_D	Creepage Distance, from pins to backside of module	3.2	---	---	mm	See outline Drawings
CTI	Comparative Tracking Index	600	---	---	-	

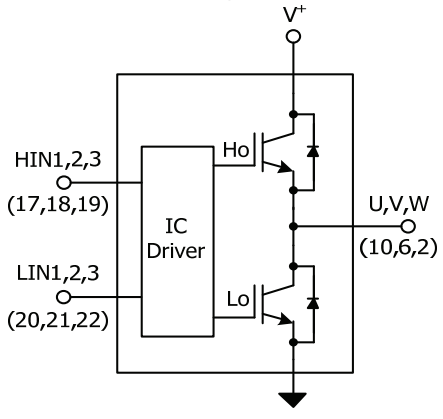
Internal NTC - Thermistor Characteristics

Parameter	Definition	Min	Typ	Max	Units	Conditions
R_{25}	Resistance	97	100	103	kΩ	T_C = 25°C
R_{125}	Resistance	2.25	2.52	2.80	kΩ	T_C = 125°C
B	B-constant (25-50°C)	4165	4250	4335	k	$R_2 = R_1 e^{[B(1/T2 - 1/T1)]}$
Temperature Range		-40	---	125	°C	
Typ. Dissipation constant		---	1	---	mW/°C	T_C = 25°C

Internal Current Sensing Resistor - Shunt Characteristics

Symbol	Parameter	Min	Typ	Max	Units	Conditions
R_{Shunt}	Resistance	72.5	73.3	74.1	mΩ	T_C = 25°C
T_{Coeff}	Temperature Coefficient	0	---	200	ppm/°C	
P_{Shunt}	Power Dissipation	---	---	2.2	W	-40°C< T_C <100°C
T_{Range}	Temperature Range	-40	---	125	°C	

Input-Output Logic Level Table



$\overline{FLT}$/EN	I_{TRIP}	HIN1,2,3	LIN1,2,3	U,V,W
1	0	1	0	V+
1	0	0	1	0
1	0	0	0	Off
1	0	1	1	Off
1	1	X	X	Off
0	X	X	X	Off

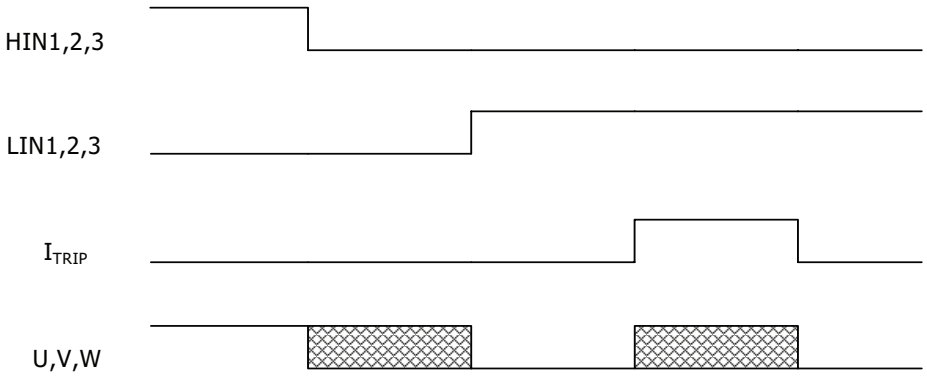


Figure 1. Input/Output Timing Diagram

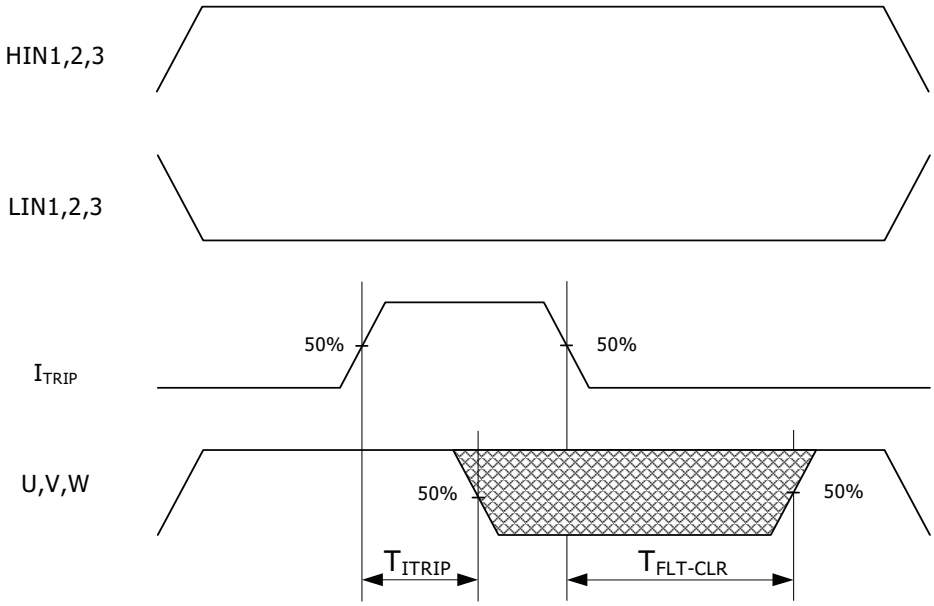


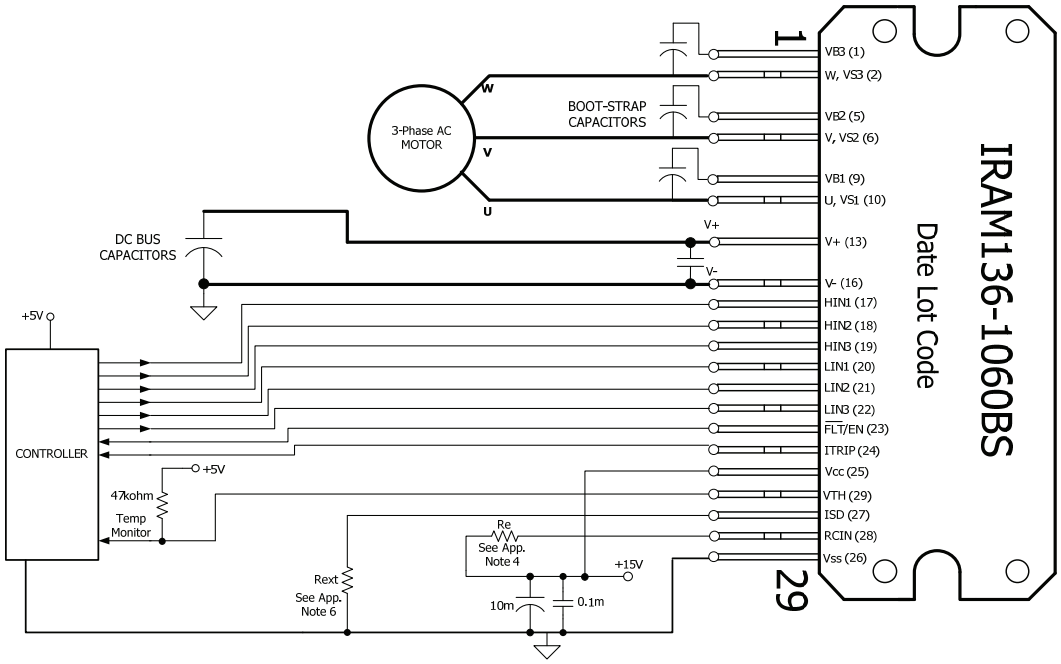
Figure 2. I_{TRIP} Timing Waveform

Note 5: The shaded area indicates that both high-side and low-side switches are off and therefore the half-bridge output voltage would be determined by the direction of current flow in the load.

Module Pin-Out Description

Pin	Name	Description
1	VB3	High Side Floating Supply Voltage 3
2	W,VS3	Output 3 - High Side Floating Supply Offset Voltage
3	na	none
4	na	none
5	VB2	High Side Floating Supply voltage 2
6	V,VS2	Output 2 - High Side Floating Supply Offset Voltage
7	na	none
8	na	none
9	VB1	High Side Floating Supply voltage 1
10	U,VS1	Output 1 - High Side Floating Supply Offset Voltage
11	na	none
12	na	none
13	V^+	Positive Bus Input Voltage
14	na	none
15	na	none
16	V-	Negative Bus Input Voltage
17	HIN1	Logic Input High Side Gate Driver - Phase 1
18	HIN2	Logic Input High Side Gate Driver - Phase 2
19	HIN3	Logic Input High Side Gate Driver - Phase 3
20	LIN1	Logic Input Low Side Gate Driver - Phase 1
21	LIN2	Logic Input Low Side Gate Driver - Phase 2
22	LIN3	Logic Input Low Side Gate Driver - Phase 3
23	$\overline{FLT}$/EN	Fault Output and Enable Pins
24	I_{FB}	Current Feedback Output Pin
25	V_{CC}	+15V Main Supply
26	V_{SS}	Negative Main Supply
27	ISD	Current Protection Level Programming Pin
28	RCIN	RCIN Reset Programming Pin
29	V_{TH}	Temperature Feedback

Typical Application Connection IRAM136-1060BS



Application Notes

1. Electrolytic bus capacitors should be mounted as close to the module bus terminals as possible to reduce ringing and EMI problems. Mounting an additional high frequency ceramic capacitor close to the module pins is highly recommended.

2. In order to provide good decoupling between VCC-VSS and VB1,2,3-VS1,2,3 terminals, the capacitors shown connected between these terminals should be located very close to the module pins. Additional high frequency capacitors, typically 0.1µF, are strongly recommended.

3. Value of the boot-strap capacitors depends upon the switching frequency and modulation techniques. Their selection should be made based on IR design tip DN 98-2a, application note AN-1044 or Figure 9. Bootstrap capacitor value must be selected to limit the power dissipation of the internal resistor in series with the VCC. (See maximum ratings Table on page 3).

4. WARNING! Please note that after approx. 32ms the FAULT is automatically reset. (See Dynamic Characteristics Table on page 5). The default Fault clear time is when RCIN pin is open. Refer to Figure 11a for Re selection and desired RCIN setting.

5. PWM generator must be disabled within automatic reset time ($T_{FLT-CLR}$) to guarantee shutdown of the system, overcurrent condition must be cleared before resuming operation.

6. ISD can be programmed by using external resistor (Rext) connected to Vss. The default current level is when ISD pin is open (see Inverter Characteristics Table on page 3). Maximum current level can be achieved by connecting ISD to Vss. See Figure 11b for desired current level and resistor selection.

7. Fault/En pin (23) must be pulled-up to +5V.

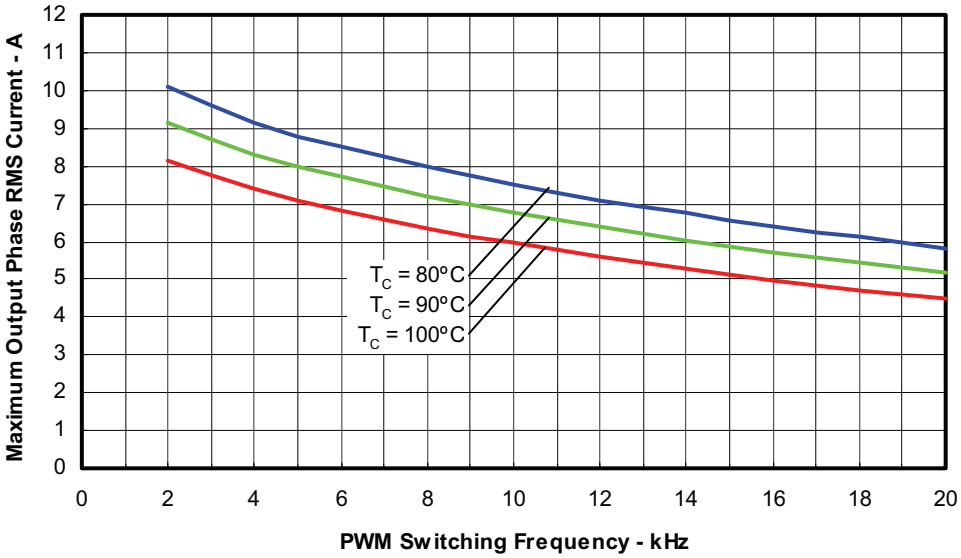


Figure 3. Maximum Sinusoidal Phase Current vs. PWM Switching Frequency
Sinusoidal Modulation, V^+=400V, T_J=150°C, MI=0.8, PF=0.6, fmod=100Hz

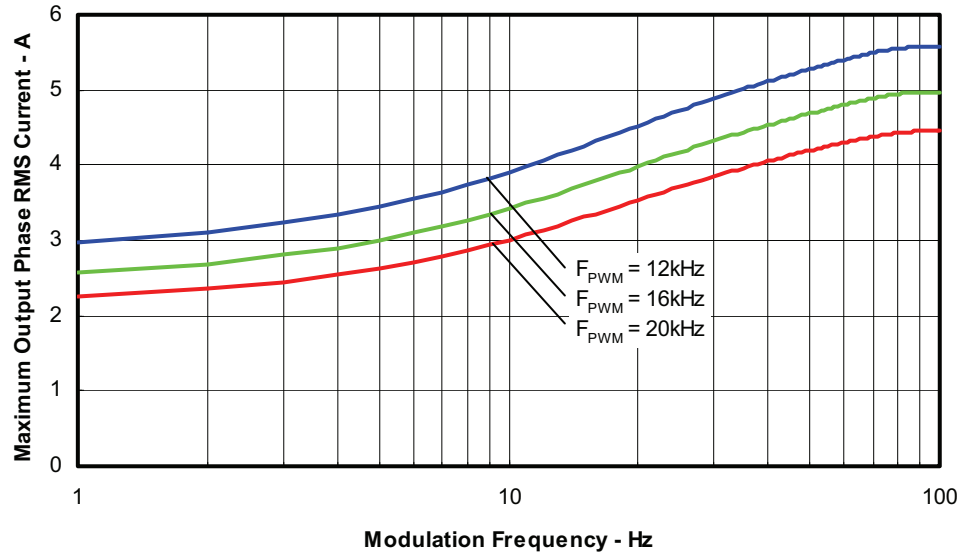


Figure 4. Maximum Sinusoidal Phase Current vs. Modulation Frequency
Sinusoidal Modulation, V^+=400V, T_J=150°C, T_C=100°C, MI=0.8, PF=0.6

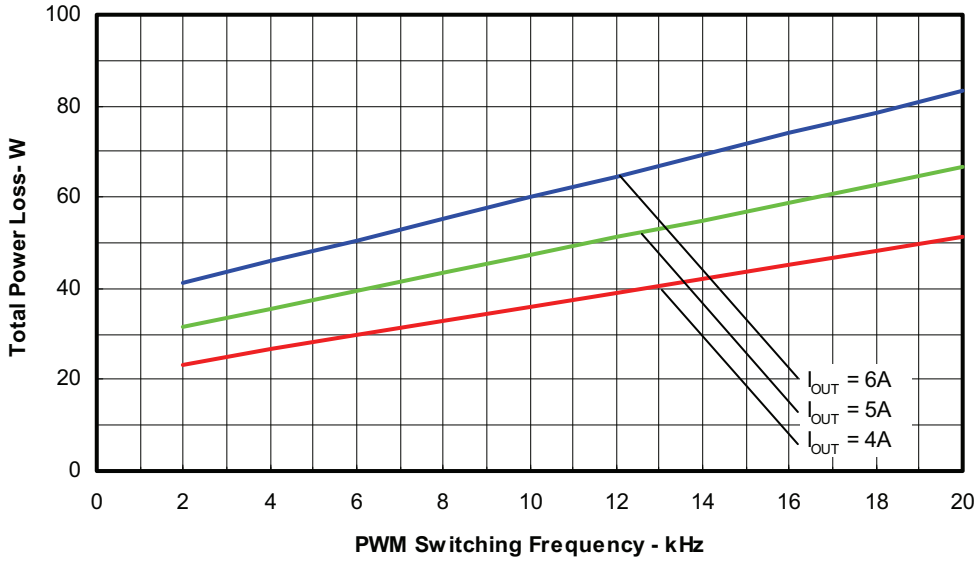


Figure 5. Total Power Losses vs. PWM Switching Frequency
Sinusoidal Modulation, V^+=400V, T_J=150°C, MI=0.8, PF=0.6, fmod=100Hz

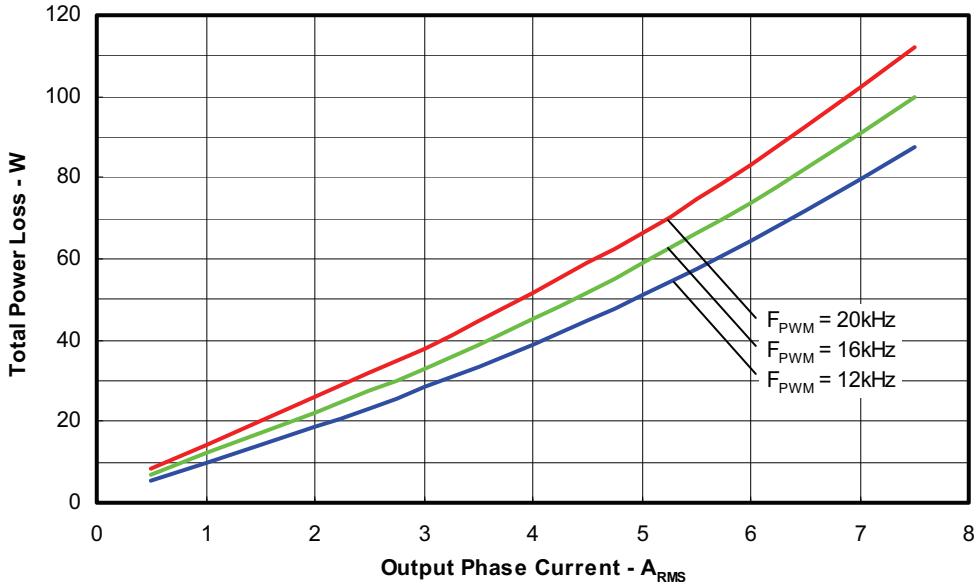


Figure 6. Total Power Losses vs. Output Phase Current
Sinusoidal Modulation, V^+=400V, T_J=150°C, MI=0.8, PF=0.6, fmod=100Hz

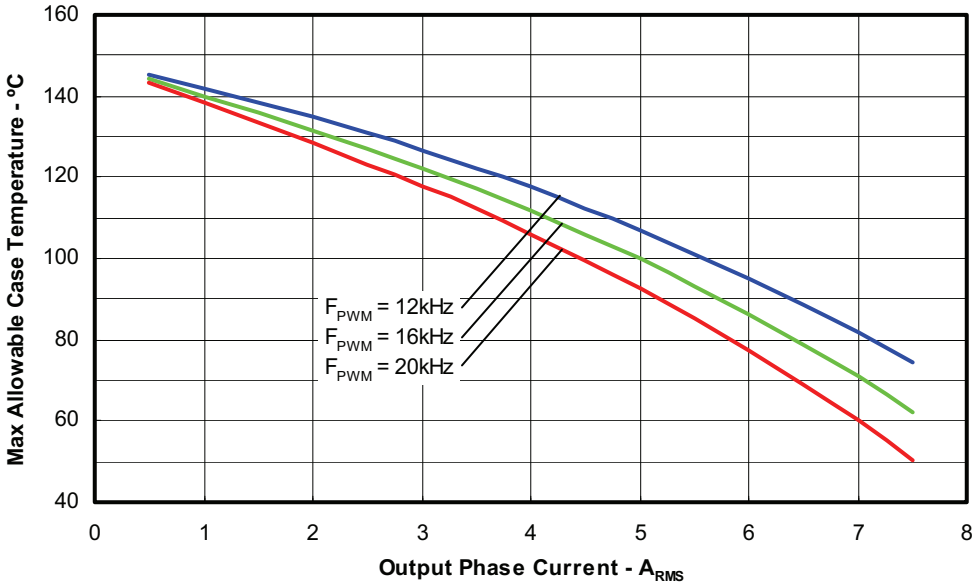


Figure 7. Maximum Allowable Case Temperature vs. Output RMS Current per Phase Sinusoidal Modulation, V^+=400V, T_J=150°C, MI=0.8, PF=0.6, fmod=50Hz

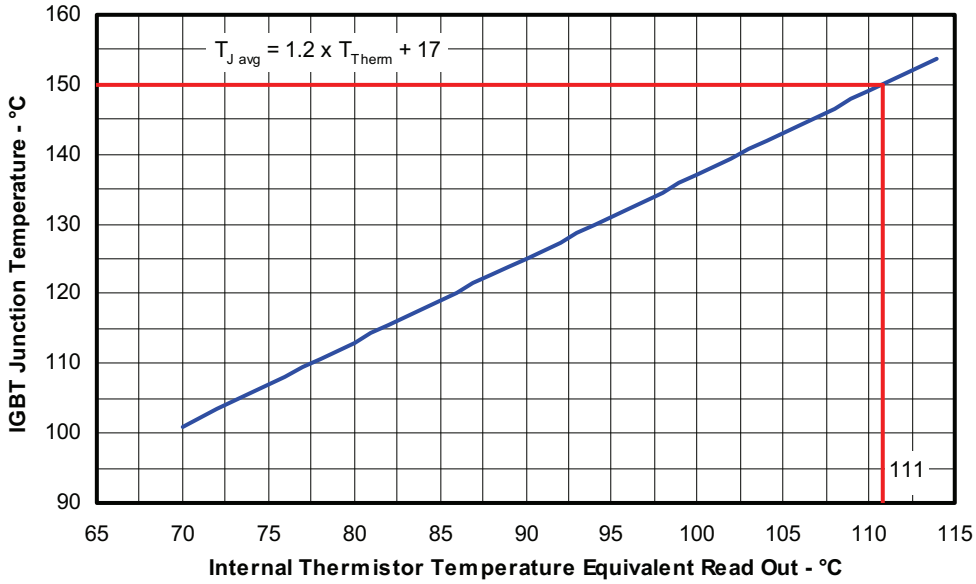
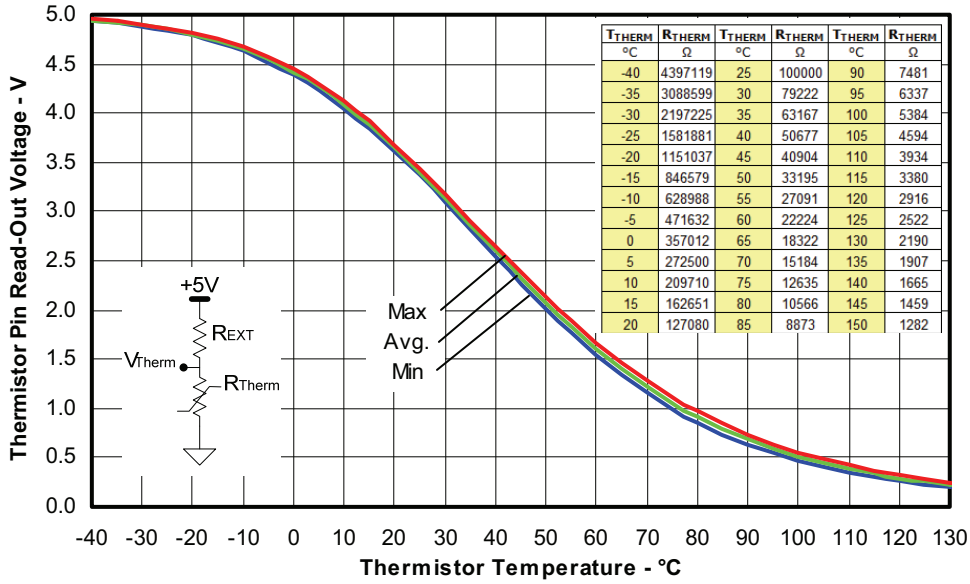


Figure 8. Estimated Maximum IGBT Junction Temperature vs. Thermistor Temperature Sinusoidal Modulation, V+=400V, Iphase=5Arms, fsw=16kHz, fmod=50Hz, MI=0.8, PF=0.6



T_{THERM} °C	R_{THERM} Ω	T_{THERM} °C	R_{THERM} Ω	T_{THERM} °C	R_{THERM} Ω
-40	4397119	25	100000	90	7481
-35	3088599	30	79222	95	6337
-30	2197225	35	63167	100	5384
-25	1581881	40	50677	105	4594
-20	1151037	45	40904	110	3934
-15	846579	50	33195	115	3380
-10	628988	55	27091	120	2916
-5	471632	60	22224	125	2522
0	357012	65	18322	130	2190
5	272500	70	15184	135	1907
10	209710	75	12635	140	1665
15	162651	80	10566	145	1459
20	127080	85	8873	150	1282

Figure 9. Thermistor Readout vs. Temperature (47kohm pull-up resistor, 5V) and Normal Thermistor Resistance values vs. Temperature Table.

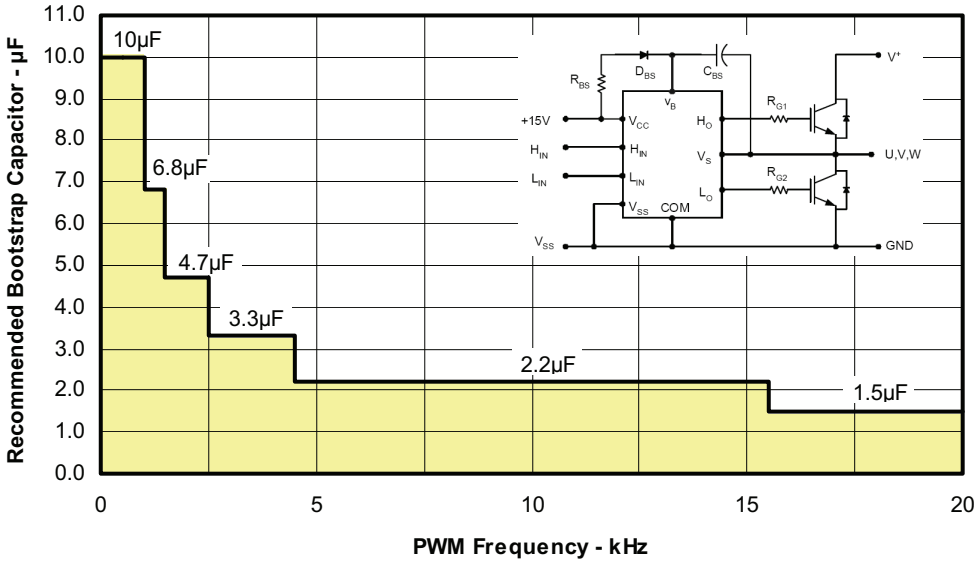


Figure 10. Recommended Bootstrap Capacitor Value vs. Switching Frequency

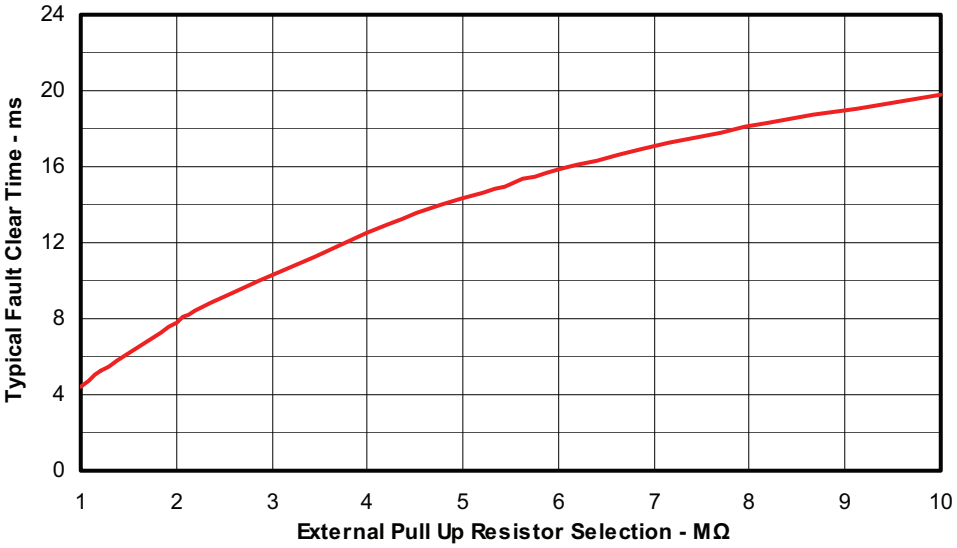


Figure 11a. External Pull Up resistor selection for Fault clear time
(Recommended minimum Pull up Resistor is 1MΩ)

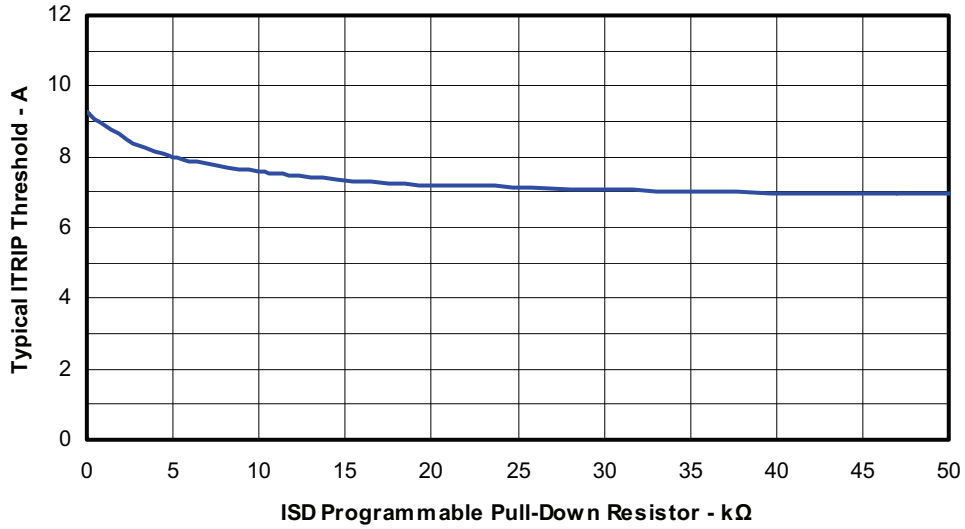


Figure 11b. Itrip Level External Pull down Resistor Selection

Figure 12. Switching Parameter Definitions

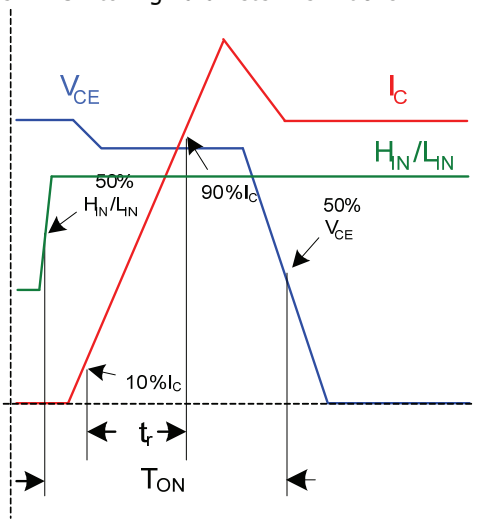


Figure 11a. Input to Output propagation turn-on delay time.

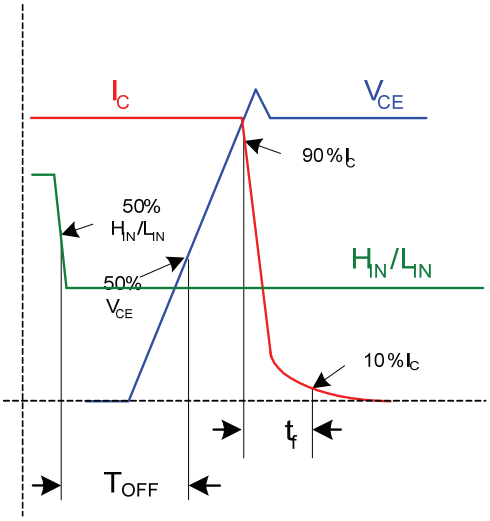


Figure 11b. Input to Output propagation turn-off delay time.

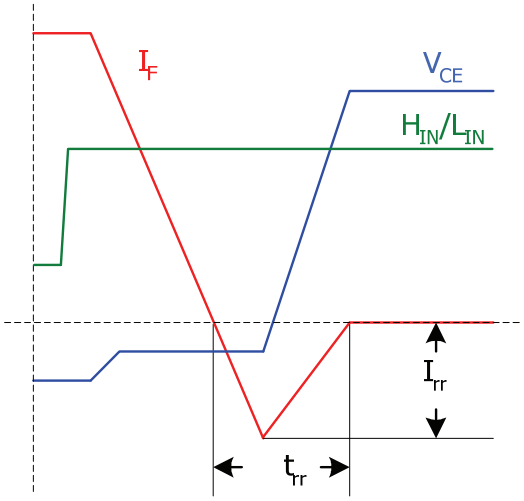
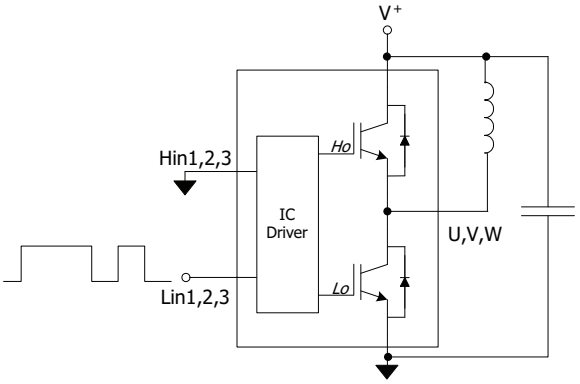


Figure 11c. Diode Reverse Recovery.



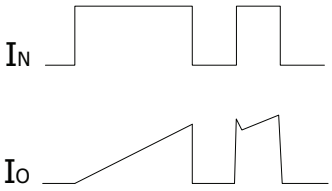
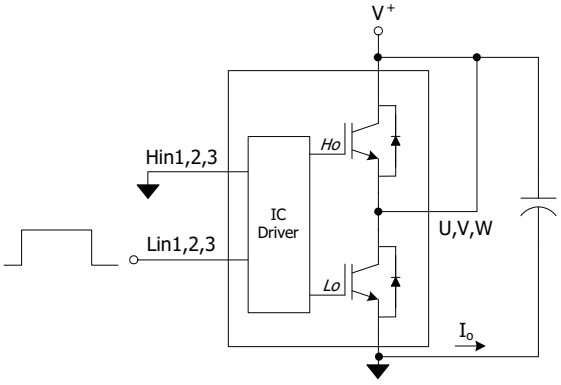


Figure CT1. Switching Loss Circuit



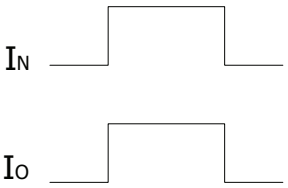
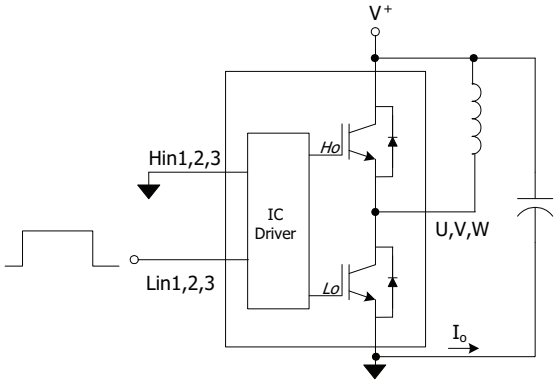


Figure CT2. S.C.SOA Circuit



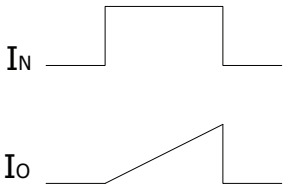
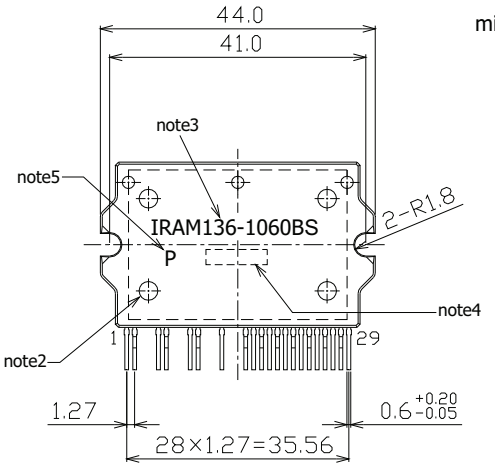
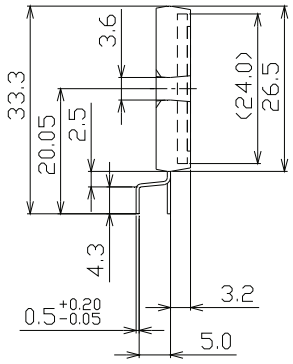


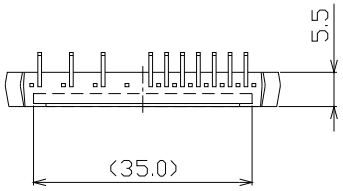
Figure CT3. R.B.SOA Circuit

Package Outline IRAM136-1060BS



missing pin : 3,4,7,8,11,12,14,15





note1: Unit Tolerance is ±0.5mm,
Unless Otherwise Specified.

note2: Mirror Surface Mark indicates Pin1 Identification.

note3: Part Number Marking.
Characters Font in this drawing differs from
Font shown on Module.

note4: Lot Code Marking.
Characters Font in this drawing differs from
Font shown on Module.

note5: "P" Character denotes Lead Free.
Characters Font in this drawing differs from
Font shown on Module.

Dimensions in mm
For mounting instruction see AN-1049

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